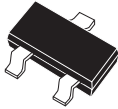


CMPTH10

NPN SILICON RF TRANSISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTH10 type is an NPN silicon RF transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for low noise UHF/VHF amplifier and high output oscillator applications.

Marking code is C3E.

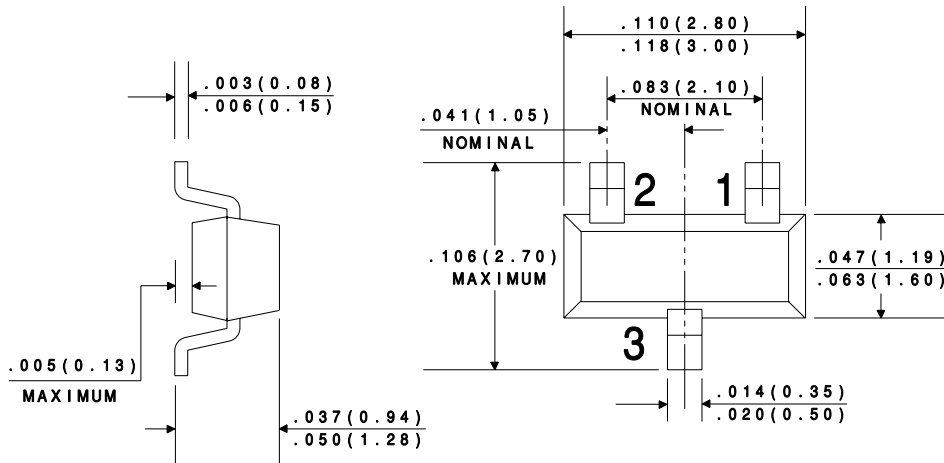
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	3.0	V
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =25V		100	nA
I _{EBO}	V _{EB} =2.0V		100	nA
BV _{CB0}	I _C =100μA	30		V
BV _{CEO}	I _C =1.0mA	25		V
BV _{EBO}	I _E =10μA	3.0		V
V _{CE(SAT)}	I _C =4.0mA, I _B =0.4mA		0.50	V
V _{BE(ON)}	V _{CE} =10V, I _B =4.0mA		0.95	V
h _{FE}	V _{CE} =10V, I _C =4.0mA	60		
f _T	V _{CE} =10V, I _C =4.0mA, f=100MHz	650		MHz
C _{cb}	V _{CB} =10V, I _E =0, f=1.0MHz		0.70	pF
C _{rb}	V _{CB} =10V, I _E =0, f=1.0MHz		0.65	pF
rb'C _c	V _{CB} =10V, I _C =4.0mA, f=31.8MHz		9.0	ps

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR